https://digital-library.theiet.org/content/journals/10.1049/el.2018.5113

Cerca

Visit www.theiet.org | My IET

Shopp

Digital Library

Search

All content

Journals & magazines | Conferences | eBooks | Reference | Subjects

Home > Journals & magazines > Electronics Letters > Volume 54, Issue 16 > Article

Layout influence on microwave performance of graphene field effect transistors

Author(s): M.A. Giambra [1] ; A. Benfante [2] ; L. Zeiss [2] ; R. Pernice [2] ; V. Miseikis [1] ; W.H.P. Pernice [3] ; M.H. Jang [4] ; J.-H. Ahn [4] ; A.C. Cino [2] ; S. Stivala [2] ; E. Calandra [2] ; A.C. Busacca [2] ; R. Danneau [5]

View affiliations

Source: Volume 54, Issue 16, 09 August 2018, p. 984 – 986

DOI: 10.1049/el.2018.5113 , Print ISSN 0013-5194, Online ISSN 1350-911X

Access Full Text

Recommend Title

Publication to library

« Previous Article | Table of contents | Next Article »

© The Institution of Engineering and Technology

Received 27/04/2018, Published 29/06/2018

Errata or comment

Article | References (16) | Cited By (0) | Supplementary material (0) | Keywords | Related Content

The authors report on an in-depth statistical and parametrical investigation on the microwave performance of graphene FETs on sapphire substrate. The devices differ for the gate-drain/source distance and for the gate length, having kept instead the gate width constant. Microwave *S*-parameters have been measured for the different devices. Their results demonstrate that the cut-off frequency does not monotonically increase with the scaling of the device geometry and that it exists an optimal region in the gate-drain/source and gate-length space which maximises the microwave performance.